

What is claim d is:

1. An LPCVD apparatus comprising: a container for
accommodating an organometallic compound, said compound
5 serving as a raw material; a heating means for heating the
container and vaporizing the organometallic compound to
obtain a raw material gas; a reactor for accommodating a
substrate on which a thin film being precipitated; an
exhaust pump for maintaining a low pressure atmosphere
10 within the reactor; and a trap provided on the upstream of
the exhaust pump and cooling used raw material gas supplied
from the reactor,

wherein said trap is provided with honeycomb-
structure cylindrical fillers in a flowing passage through
15 which the used raw material flows.

2. The LPCVD apparatus according to claim 1, wherein
the length of the honeycomb-structure cylindrical fillers is
in a range of 0.01 to 1.0 m in a direction along which the
20 used raw material flows.

3. The LPCVD apparatus according to claim 1 or 2,
wherein the honeycomb-structure cylindrical fillers have
holes with a maximum diameter of 0.5 to 10 mm.

4. The LPCVD apparatus according to claims 1 to 3,

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